



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

SFT1202 — NPN Epitaxial Planar Silicon Transistor

High-Voltage Switching Applications

Applications

- DC / DC converter, relay drivers, lamp drivers, motor drivers, inverter

Features

- Adoption of FBET, MBIT process
- Low collector-to-emitter saturation voltage
- High allowable power dissipation
- Large current capacity
- High-speed switching

Specifications

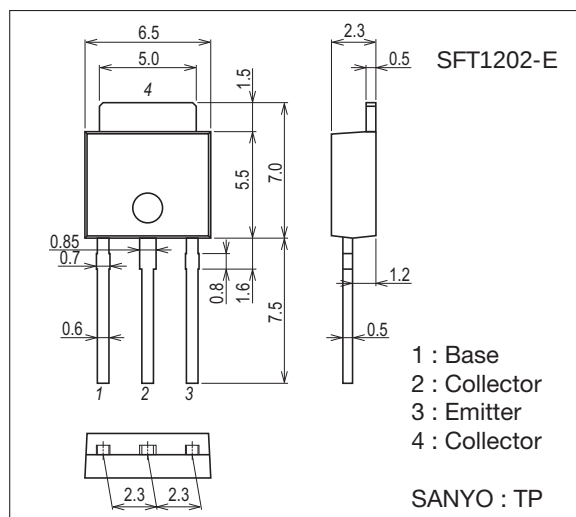
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		180	V
Collector-to-Emitter Voltage	VCES		180	V
Collector-to-Emitter Voltage	VCEO		150	V
Emitter-to-Base Voltage	VEBO		7	V
Collector Current	IC		2	A
Collector Current (Pulse)	ICP		3	A
Base Current	IB		400	mA

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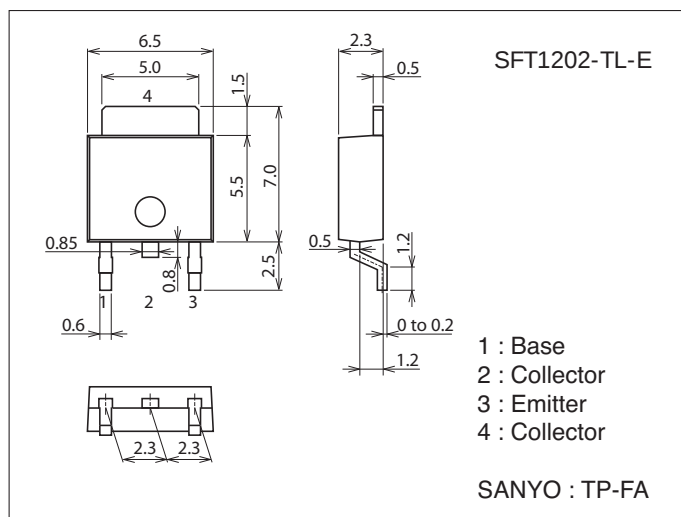
Package Dimensions unit : mm (typ)

7518-003



Package Dimensions unit : mm (typ)

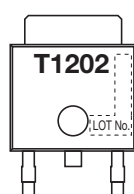
7003-003



Product & Package Information

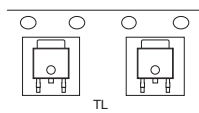
- Package : TP
- JEITA, JEDEC : SC-64, TO-251
- Minimum Packing Quantity : 500 pcs./bag

Marking (TP, TP-FA)

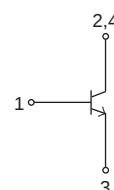


- Package : TP-FA
- JEITA, JEDEC : SC-63, TO-252
- Minimum Packing Quantity : 700 pcs./reel

Packing Type (TP-FA) : TL



Electrical Connection



SANYO Semiconductor Co., Ltd.

<http://www.sanyosemi.com/en/network/>

SFT1202

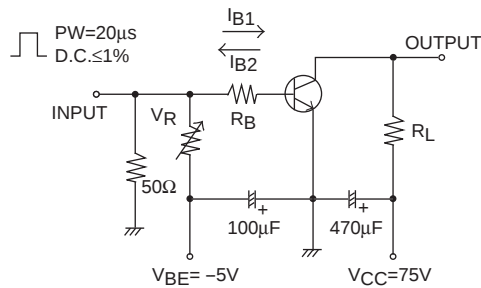
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Parameter	Symbol	Conditions	Ratings	Unit
Collector Dissipation	P _C		1	W
		T _c =25°C	15	W
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at T_a=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CBO}	V _{CB} =80V, I _E =0A			1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =4V, I _C =0A			1	μA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =100mA	200		560	
Gain-Bandwidth Product	f _T	V _{CE} =10V, I _C =300mA		140		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		12		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)1}	I _C =1A, I _B =100mA		110	165	mV
	V _{CE(sat)2}	I _C =0.5A, I _B =50mA		65	100	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =1A, I _B =100mA		0.85	1.2	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	I _C =10μA, I _E =0A	180			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CES}	I _C =100μA, R _{BE} =0Ω	180			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =1mA, R _{BE} =∞	150			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =10μA, I _C =0A	7			V
Turn-ON Time	t _{on}	See specified Test Circuit.		50		ns
Storage Time	t _{stg}			1460		ns
Fall Time	t _f			70		ns

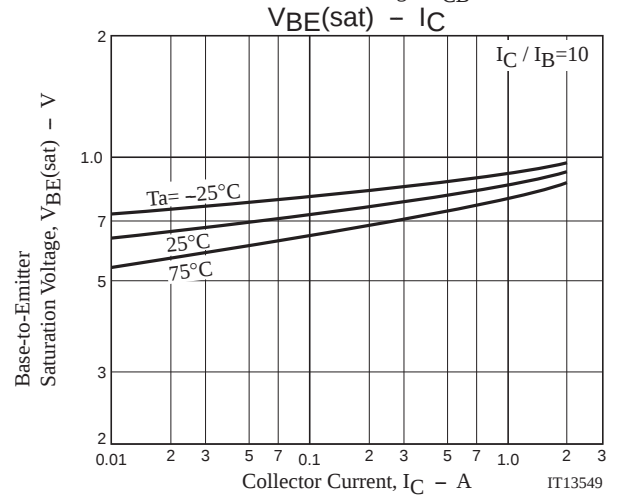
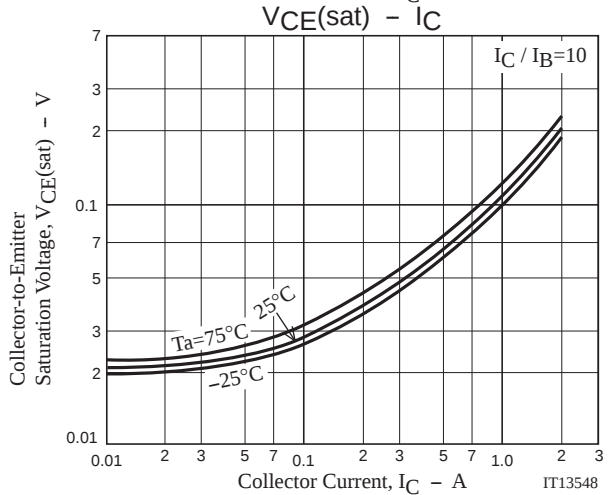
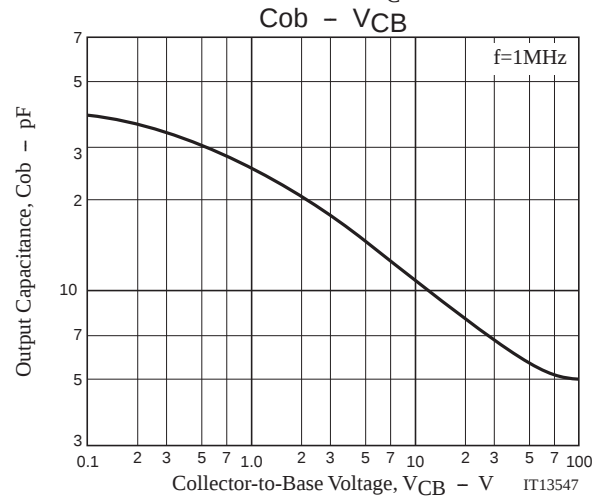
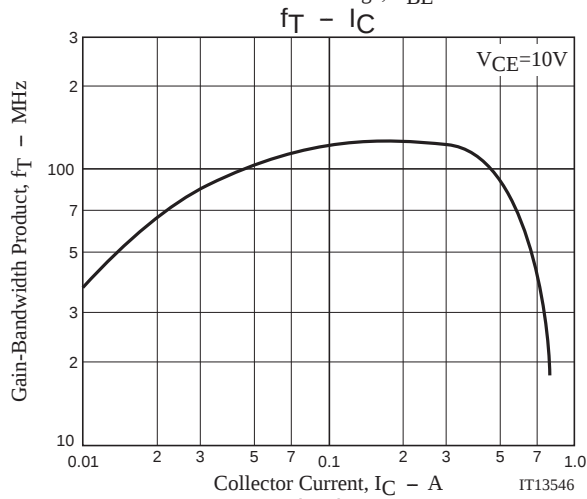
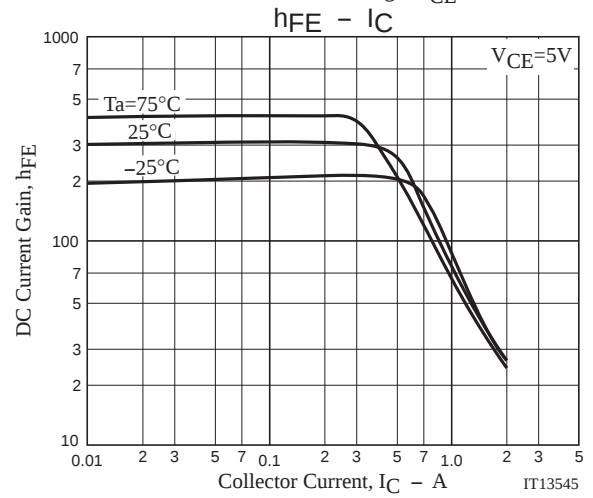
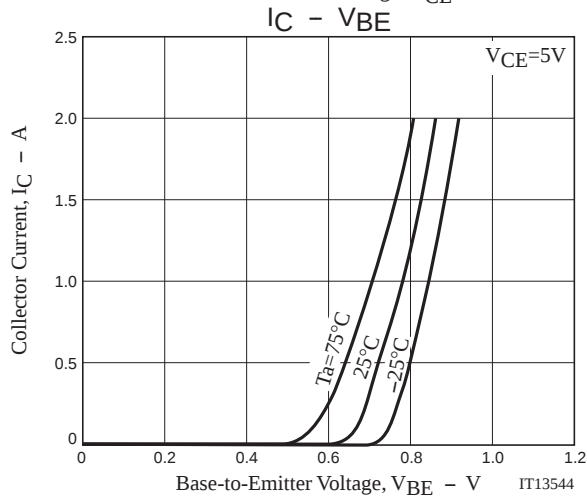
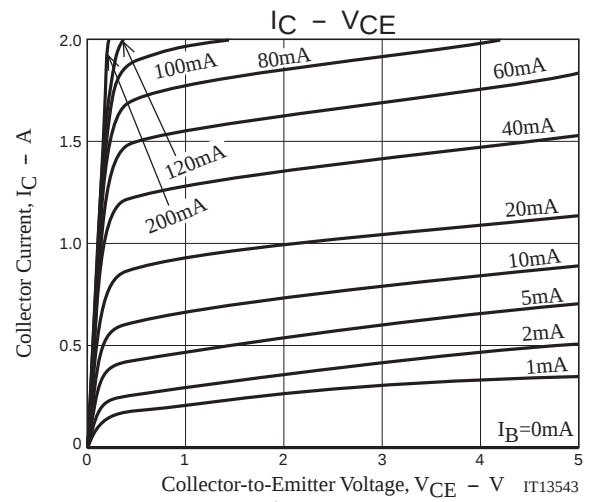
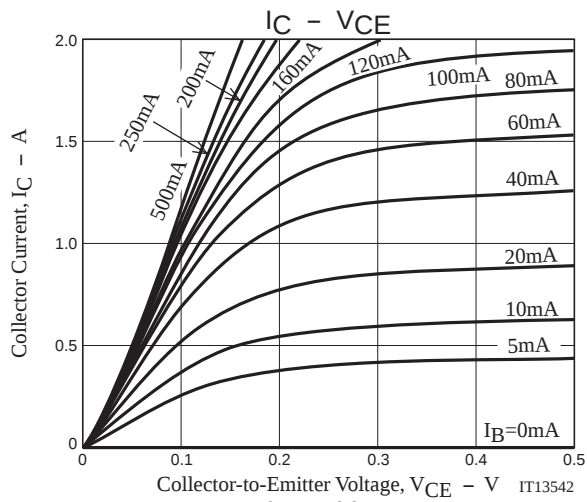
Switching Time Test Circuit

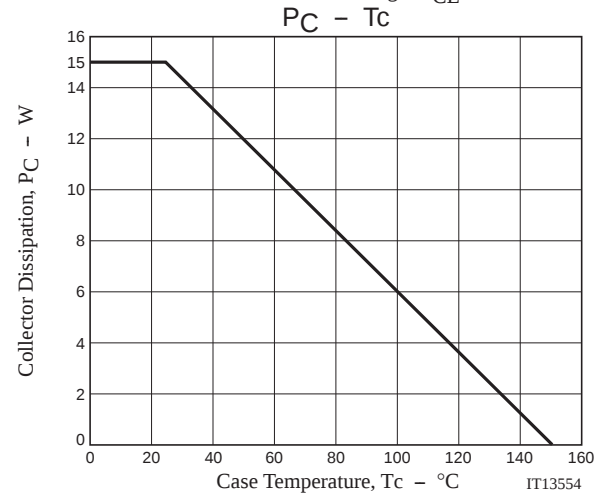
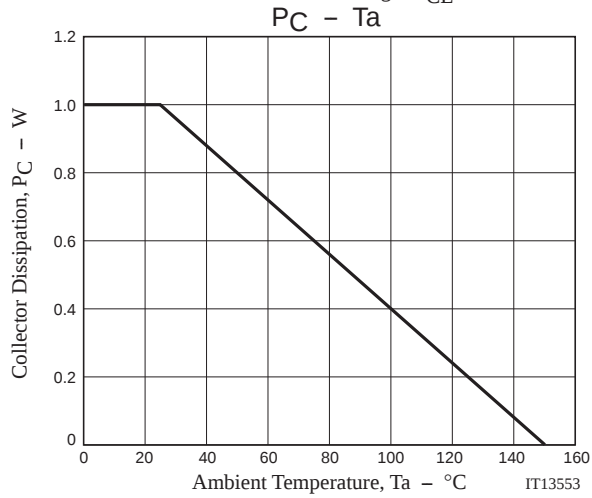
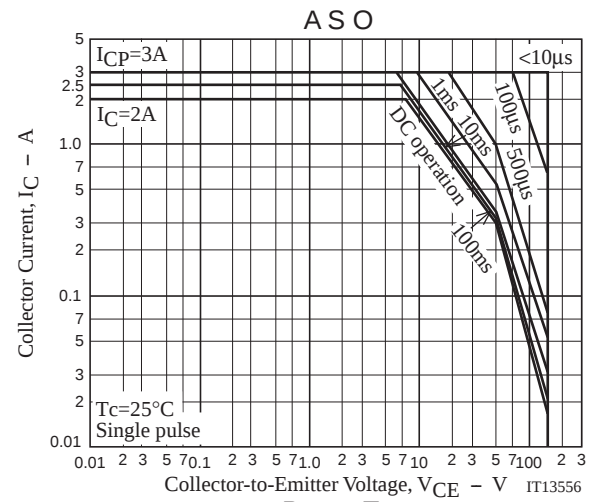
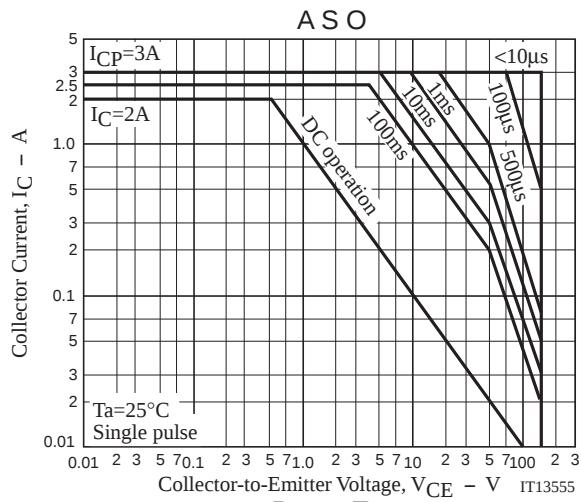


$$I_C = 10I_{B1} = -10I_{B2} = 0.5A$$

Ordering Information

Device	Package	Shipping	memo
SFT1202-E	TP	500pcs./bag	Pb Free
SFT1202-TL-E	TP-FA	700pcs./reel	





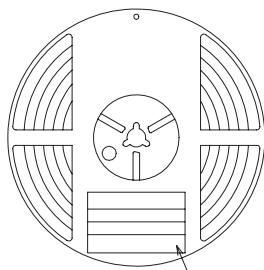
Taping Specification

SFT1202-TL-E

Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
TP-FA	TP	700	2,100	12,600	3 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label

Type No.
LOT No.
Quantity
Origin

Reel label, Inner box label
(unit:mm)

(P) TYPE	000000000
(1) LOT	00
(Q) QTY	0,000 (1) LEAD FREE *
(Z) SPECIAL	*20722005310C*
ASSEMBLY:****	(DIFFUSION:****)

Outer box label

It is a label at the time of factory shipments.
The form of a label may change in physical
distribution process.

TYPE CODE	
TYPE	○○○○○○○○
QTY	0,000 PCS (1) LEAD FREE *
LOT	○○○○○○○○
PACKAGE	○○○○○○○○
SPECIAL	
ASSEMBLY:****	(DIFFUSION:****)

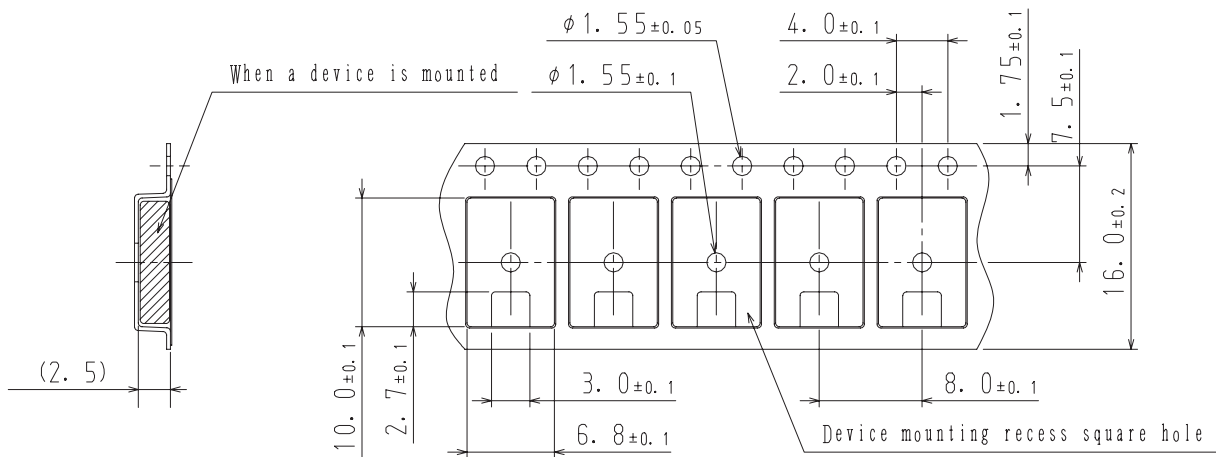
NOTE (1)

The LEAD FREE * description shows that the surface
treatment of the terminal is lead free.

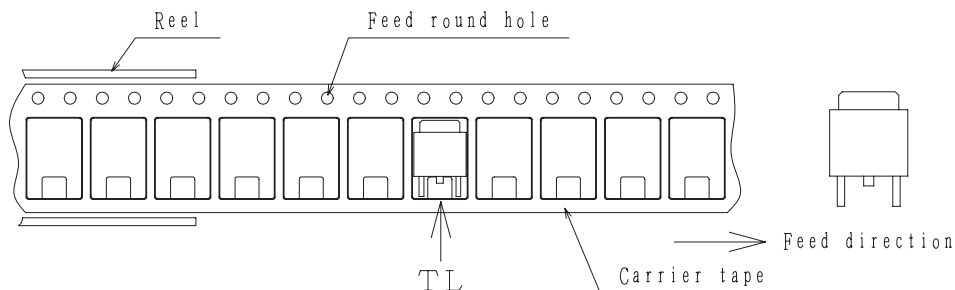
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

Taping configuration

1. Carrier tape size (unit:mm)



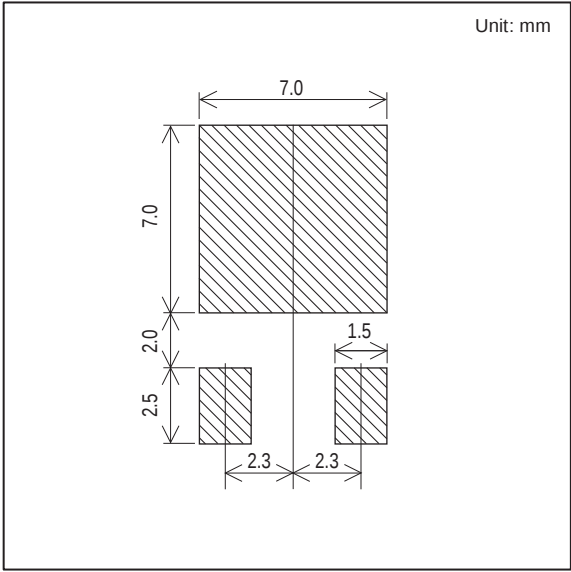
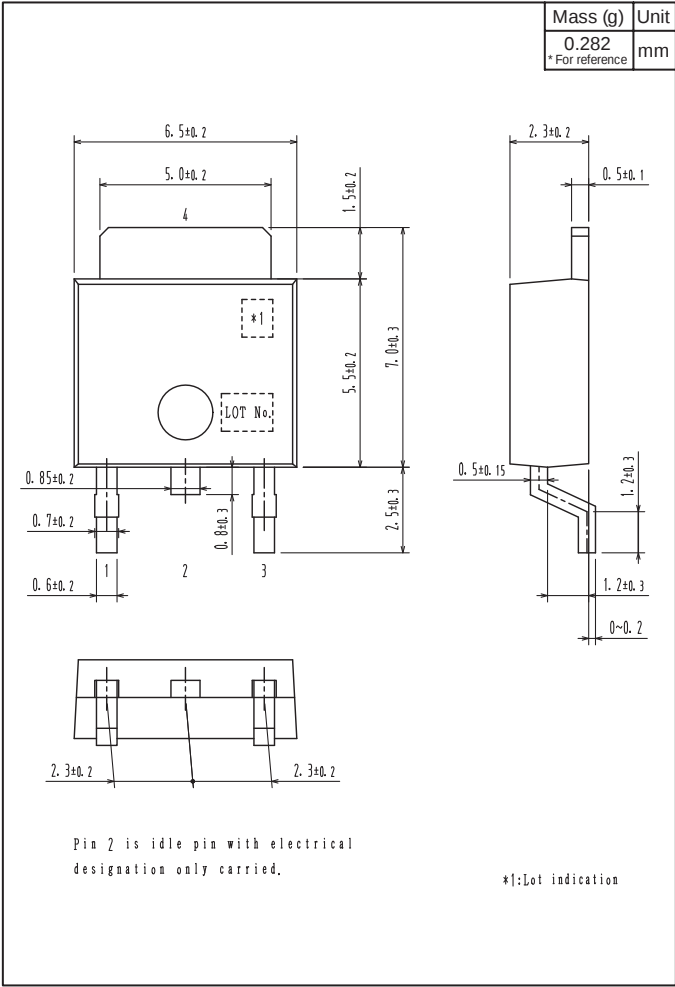
2. Device placement direction



Those with one electrode terminal on the feed hole side.....TL

Outline Drawing
SFT1202-TL-E

Land Pattern Example

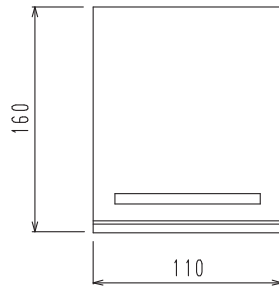
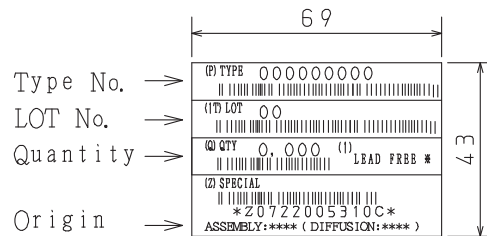


Bag Packing Specification

SFT1202-E

1. Packing Format

Package Name	Maximum Number of devices contained (pcs)			
	Bag	Inner box	Outer box	
TP	500	B-1	A-1	A-2
		10, 000	50, 000	30, 000
Packing format (Dimensions:mm (external))				
		Inner box	Outer box	
		B-1	A-1	A-2
		445×225×55	470×250×300	470×250×190

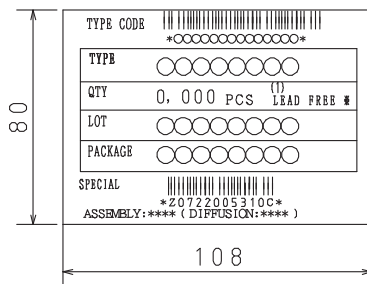
2. Bag dimensions
(unit:mm)3. Bag label, Inner box label
(unit:mm)4. Outer box label
(unit:mm)

It is a label at the time of factory shipments.
The form of a label may change in physical
distribution process,

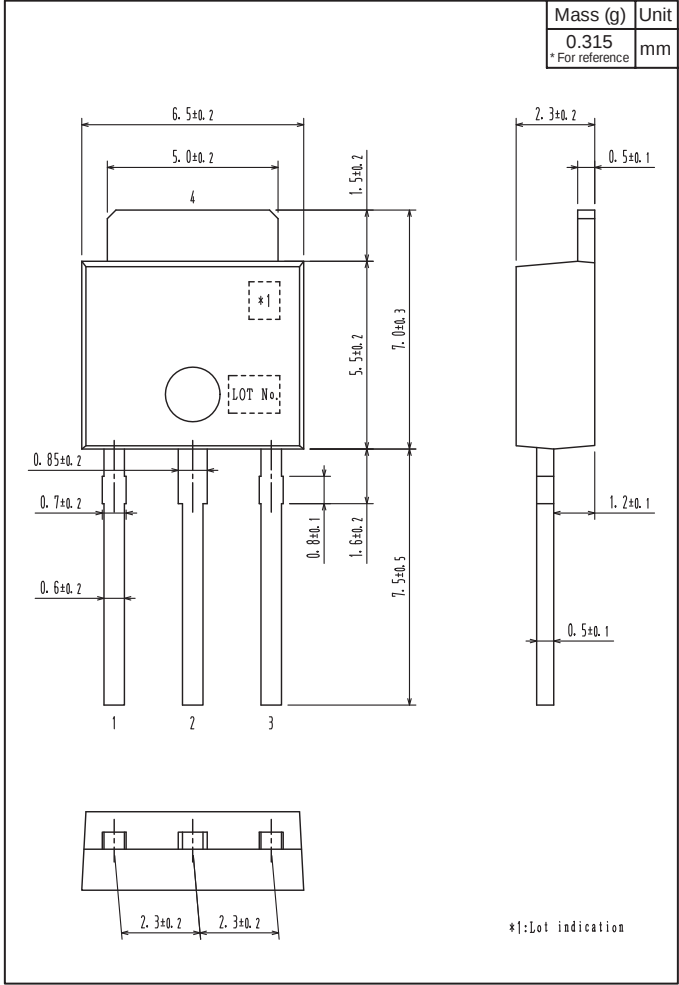
NOTE (1)

The LEAD FREE * description shows that the
surface treatment of the terminal is lead free.

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3



Outline Drawing
SFT1202-E



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